The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A display device comprising:

a plurality of pixel portions each having an active device and arranged in matrix and each having a pixel electrode over a substrate; and

a plurality of sensor portions arranged in matrix over said substrate,

~~wherein a plane parallel to a direction of said matrix is divided into at least a first display region and a second display region in said pixel electrode,~~

wherein said pixel electrode comprises a first layer and a second layer, said second layer provided over said first layer,

wherein one of said first layer and said second layer of said pixel electrode comprises a reflecting material ~~in said first display region~~,

wherein the other of said first layer and said second layer of said pixel electrode comprises a light-transmitting material ~~in said second display region~~, and

wherein each of said sensor portions includes a photo-electric conversion device, and can read information by utilizing the rays of light transmitting through said light-transmitting material when an external image is read.

2. (Original) An apparatus according to claim 1, wherein said active device comprises a bottom gate type TFT.

3. (Original) An apparatus according to claim 1, wherein said active device comprises a top gate type TFT.

4. (Currently Amended) A display device comprising:

a plurality of pixel portions each having an active device and arranged in matrix and each having a pixel electrode over a first substrate; and

a plurality of sensor portions disposed in matrix over a second substrate opposed to said first substrate,

wherein ~~a plane parallel to a direction of said matrix is divided into at least a first display region and a second display region in said pixel electrode,~~

wherein said pixel electrode comprises a first layer and a second layer, said second layer provided over said first layer,

wherein one of said first layer and said second layer of said pixel electrode comprises a reflecting material ~~in said first display region~~,

wherein the other of said first layer and said second layer of said pixel electrode comprises a light-transmitting material ~~in said second display region~~, and

wherein each of said sensor portions has a photo-electric conversion device, and can read information by utilizing the rays of light transmitting through said light-transmitting material when an external image is read.

5. (Original) An apparatus according to claim 4, wherein color filters are disposed on said opposed substrate.

6. (Original) An apparatus according to claim 4, wherein said active device comprises a bottom gate TFT.

7. (Original) An apparatus according to claim 4, wherein said active device comprises a top gate type TFT.

8. (Currently Amended) A display device comprising:

a plurality of pixel portions each having an active device and arranged in matrix and each having a pixel electrode over a substrate; and

a plurality of sensor portions arranged in matrix over said substrate, wherein

each of said sensor portions has a photo-electric conversion device, and at least a part of said photo-electric conversion device is extended in such a manner as to overlap with said active device,

wherein ~~a plane parallel to a direction of said matrix is divided into at least a first display region and a second display region in said pixel electrode,~~

wherein said pixel electrode comprises a first layer and a second layer, said second layer provided over said first layer,

wherein one of said first layer and said second layer of said pixel electrode comprises a reflecting material ~~in said first display region~~, and

wherein the other of said first layer and said second layer of said pixel electrode comprises a light-transmitting material ~~in said second display region~~.

9. (Original) An apparatus according to claim 8, wherein said active device comprises a top gate type TFT.

10. (Previously Presented) A display device comprising:

a plurality of pixel portions each comprising a transistor and arranged in matrix over a substrate;

a plurality of sensor portions arranged in matrix over said substrate and comprising an upper electrode and a lower electrode and a photoelectric conversion layer provided between said upper electrode and said lower electrode;

an insulation film provided over said upper electrode; and

a pixel electrode provided over said insulation film and connected with one of a source region and a drain region of said transistor;

wherein said pixel electrode overlaps with said upper electrode with said insulation film therebetween to provide a capacitance.

11. (Original) An apparatus according to claim 10, wherein a reflecting material and a light-transmitting material are used for a pixel electrode of each said pixel portions.

12. (Currently Amended) A semiconductor device comprising:

a pixel portion having an active device and a pixel electrode over a substrate; and

a sensor portion provided over said substrate and comprising a photo-electric conversion device,

wherein said active device and said pixel electrode and said photo-electric conversion device are provided in one of pixels arranged in matrix,

wherein ~~a plane parallel to a direction of said matrix is divided into at least a first display region and a second display region in said pixel electrode,~~

wherein said pixel electrode comprises a first layer and a second layer, said second layer provided over said first layer,

wherein one of said first layer and said second layer of said pixel electrode comprises a reflecting material ~~in said first display region~~,

wherein the other of said first layer and said second layer of said pixel electrode comprises a light-transmitting material ~~in said second display region~~, and

wherein said sensor portion can read information by utilizing the rays of light transmitting through said light-transmitting material when an external image is read.

13. (Original) An apparatus according to claim 12, wherein said active device comprises a bottom gate type TFT.

14. (Original) An apparatus according to claim 12, wherein said active device comprises a top gate type TFT.

15. (Currently Amended) A semiconductor device comprising:

a first substrate and a second substrate opposed to said first substrate;

a pixel portion having an active device and a pixel electrode over said first substrate; and

a sensor portion provided over said second substrate and comprising a photo-electric conversion device,

wherein said active device and said pixel electrode and said photo-electric conversion device are provided in one of pixels arranged in matrix,

~~wherein a plane parallel to a direction of said matrix is divided into at least a first display region and a second display region in said pixel electrode,~~

wherein said pixel electrode comprises a first layer and a second layer, said second layer provided over said first layer,

wherein one of said first layer and said second layer of said pixel electrode comprises a reflecting material ~~in said first display region~~,

wherein the other of said first layer and said second layer of said pixel electrode comprises a light-transmitting material ~~in said second display region~~, and

wherein said sensor portion can read information by utilizing the rays of light transmitting through said light-transmitting material when an external image is read.

16. (Original) An apparatus according to claim 15, wherein color filters are disposed on said opposed substrate.

17. (Original) An apparatus according to claim 15, wherein said active device comprises a bottom gate type TFT.

18. (Original) An apparatus according to claim 15, wherein said active device comprises a top gate type TFT.

19. (Currently Amended) A semiconductor device comprising:

a pixel portion having an active device and a pixel electrode over a substrate; and

a sensor portion provided over said substrate and having a photo-electric conversion device,

wherein said active device and said pixel electrode and said photo-electric conversion device are provided in one of pixels arranged in matrix, and

wherein at least a part of said photo-electric conversion device is extended in such a manner as to overlap with said active device,

wherein a plane parallel to a direction of said matrix is divided into at least a first display region and a second display region in said pixel electrode,

wherein said pixel electrode comprises a first layer and a second layer, said second layer provided over said first layer,

wherein one of said first layer and said second layer of said pixel electrode comprises a reflecting material ~~in said first display region~~, and

wherein the other of said first layer and said second layer of said pixel electrode comprises a light-transmitting material ~~in said second display region~~.

20. (Original) An apparatus according to claim 18, wherein said active device comprises a top gate type TFT.

21. (Previously Presented) A semiconductor device comprising:

a pixel portion comprising a transistor provided over a substrate; and

a sensor portion provided over said substrate and comprising an upper electrode and a lower electrode and a photoelectric conversion layer provided between said upper electrode and said lower electrode;

an insulation film provided over said upper electrode; and

a pixel electrode provided over said insulation film and connected with one of a source region and a drain region of said transistor;

wherein said pixel electrode overlaps with said upper electrode with said insulation film therebetween to provide a capacitance.

22. (Original) An apparatus according to claim 21, wherein a reflecting material and a light-transmitting material are used for a pixel electrode of said pixel portion.

23. (Currently Amended) A display device comprising:

a plurality of pixel portions each having an active device and arranged in matrix and each having a pixel electrode over a substrate; and

a plurality of sensor portions arranged in matrix over said substrate,

~~wherein a plane parallel to a direction of said matrix is divided into at least a first display region and a second display region in said pixel electrode,~~

wherein said pixel electrode comprises a first layer and a second layer, said second layer provided over said first layer,

wherein one of said first layer and said second layer of said pixel electrode comprises a reflecting material ~~in said first display region~~,

wherein the other of said first layer and said second layer of said pixel electrode comprises a light-transmitting material ~~in said second display region~~, and

wherein each of said sensor portions includes a photo-electric conversion device, and can read information by utilizing the rays of light transmitting through said light-transmitting material when an external image is read.

24. (Currently Amended) A display device comprising:

a plurality of pixel portions each having an active device and arranged in matrix and each having a pixel electrode over a first substrate; and

a plurality of sensor portions disposed in matrix over a second substrate opposed to said first substrate,

~~wherein a plane parallel to a direction of said matrix is divided into at least a first display region and a second display region in said pixel electrode,~~

wherein said pixel electrode comprises a first layer and a second layer, said second layer provided over said first layer,

wherein one of said first layer and said second layer of said pixel electrode comprises a reflecting material ~~in said first display region~~,

wherein the other of said first layer and said second layer of said pixel electrode comprises a light-transmitting material ~~in said second display region~~, and

wherein each of said sensor portions has a photo-electric conversion device, and can read information by utilizing the rays of light transmitting through said light-transmitting material when an external image is read.

25. (Previously Presented) A display device comprising:

a plurality of pixel portions each having an active device and arranged in matrix and each having a pixel electrode over a substrate; and

a plurality of sensor portions arranged in matrix over said substrate, wherein each of said sensor portions has a photo-electric conversion device, and at least a part of said photo-electric conversion device is extended in such a manner as to overlap with said active device.

26.-28. (Canceled)

29. (New) A device according to claim 1 wherein said pixel electrode has an image display function.

30. (New) A device according to claim 4 wherein said pixel electrode has an

image display function.

31. (New) A device according to claim 8 wherein said pixel electrode has an image display function.

32. (New) A device according to claim 12 wherein said pixel electrode has an image display function.

33. (New) A device according to claim 15 wherein said pixel electrode has an image display function.

34. (New) A device according to claim 19 wherein said pixel electrode has an image display function.

35. (New) A device according to claim 23 wherein said pixel electrode has an image display function.

36. (New) A device according to claim 24 wherein said pixel electrode has an image display function.

37. (New) A device according to claim 25 wherein said pixel electrode has an image display function.